

# Wide Bandgap Semiconductor Technology

## *For Energy Efficiency*



U.S. DEPARTMENT OF  
**ENERGY**

Energy Efficiency &  
Renewable Energy

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US Department of Energy

# Collaborators

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- **Laura Marlino, Oak Ridge National Laboratory**
- **Booz Allen Hamilton**
  - **Pawel Gradzki**
  - **Zia Rahman**
- **Al Hefner, NIST**
- **Nick Lalena, Insight Global**
- **PowerAmerica**
  - **Victor Veliadis**
  - **John Muth**
  - **Nick Justice**
- **Department of Energy**
  - **Mark Johnson**
  - **Robert Ivester**
  - **Steven Boyd**

# Presentation Outline

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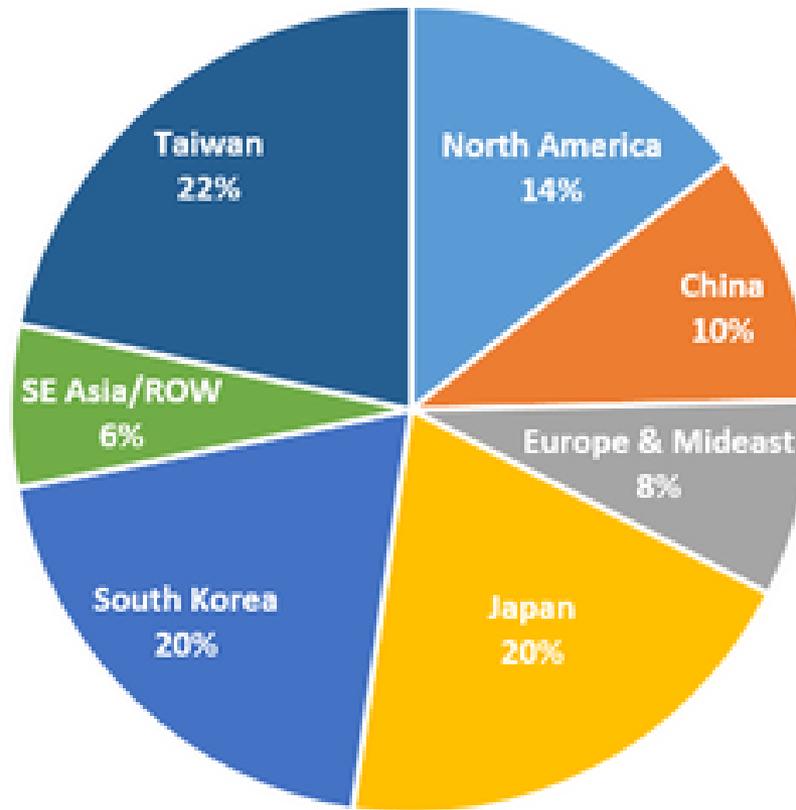
- **Decline of Si Manufacturing Industry in U.S.**
- **PowerAmerica Institute**
  - **Foundry Model**
  - **Work Force Development**
- **Cost of SiC Components**
- **Cosmic Ray Ruggedness of SiC**
- **Graduate Traineeships**
- **Achieving >50% Renewable Grid**
  - **Significance of High Voltage SiC Devices**

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# *US Manufacturing Challenge*

# U.S. Semiconductor Industry

## 2015 Worldwide Fab Capacity by Region



Source: SEMI ([www.semi.org](http://www.semi.org))

# Historical Perspective

- 1960s
  - U.S. Semiconductor industry begins offshoring labor intensive manufacturing operations.
- 1970s-1980s
  - Increased offshoring of complex operations, including wafer fabrication, design work and R&D.
- 2007
  - Only 8% of all new semiconductor fabrication plants under construction in the world were located in the U.S.
  - 12% of new fabrication plants were being built in China, 40% in Taiwan, and 6% in South Korea.
  - United States produced 17% of the world output of semiconductors, in 1995 the U.S. accounted for 23% of the global output
- 2009
  - 16 Fabs began construction throughout the world, only 1 in the U.S.
  - United States down to 14% of global semiconductor production

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# *PowerAmerica*

## Vision

*Energy savings through deployment of WBG  
Power Electronics & Development of a  
Manufacturing Base in the US through:*

- Achieving low prices of WBG devices in 5 years
- Training Graduate students in the use of WBG Semiconductors

**PowerAmerica started operations on Feb. 01, 2015  
with \$140 M funding over 5 years**

- ***High Cost of WBG Chips***

- Lower systems cost arguments don't work with 10x higher semiconductor cost

***Must reduce cost of WBG Semiconductors – Achieve 10 cents/Amp for 1.2 kV Switches in 5 years***

- ***PE Community slow to change and adapt new technologies***

- Lack of experience with WBG semiconductors
- False perceptions of poor reliability of WBG semiconductors

***Must train Graduate students to use WBG devices in Power Electronics***

## Institute Lead

North Carolina State University

## Universities

Arizona State University

Florida State University

Kettering University

Rensselaer Polytechnic Institute

University of California, Santa Barbara

University of California, Davis

Virginia Polytechnic Institute

## Laboratories

National Renewable Energy Laboratory

U.S. Naval Research Laboratory

Argonne National Laboratory

## Industry

ABB

AgileSwitchAtom Power

CoolCad Electronics

Delphi

GeneSiC

John Deere Electronic Solutions

Lockheed Martin

Monolith Semiconductor

Navitas

Power Electronics Industry Collaborative

Qorvo

Raytheon

Toshiba

Transphorm

United Silicon Carbide, Inc

Wolfspeed (formerly CREE + APEI)

X-Fab

## Pending

Auburn University

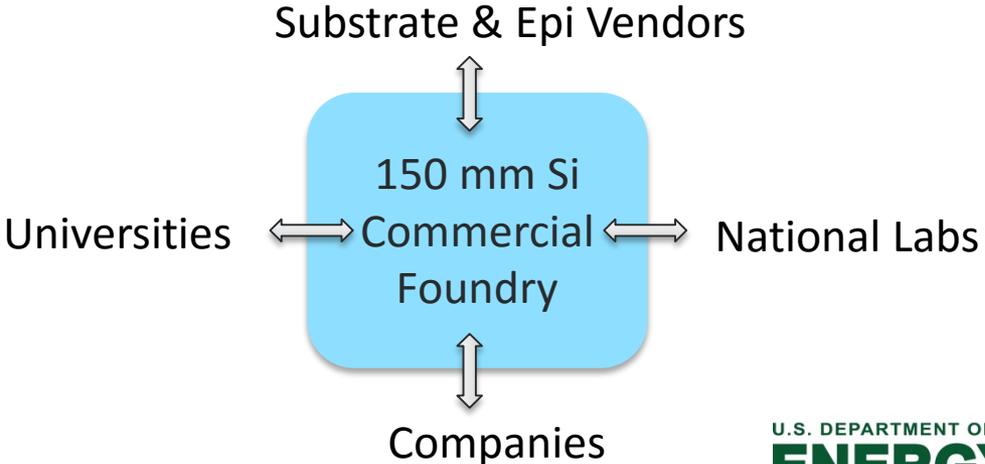
General Motors – Powertrain

InnoCit

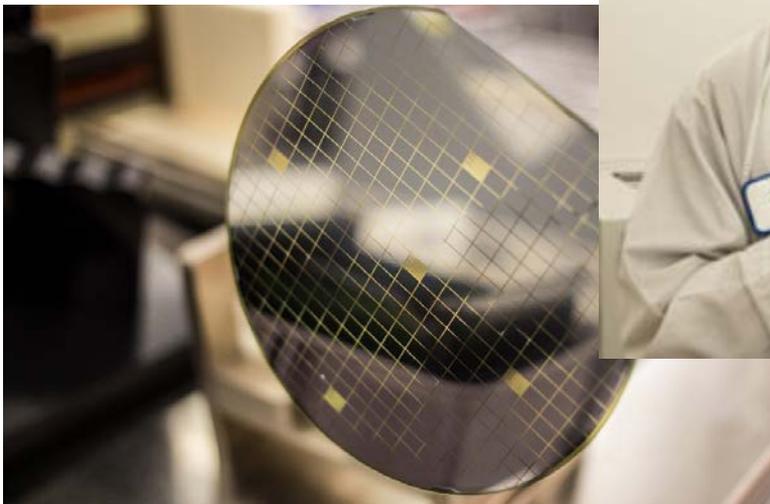
The Ohio State University

# Goal: Achieve 10 ¢/A for 1.2 kV Switches in 5 yrs

- Combine common Si and SiC process lines
  - 90% are the same
- Aggregate Substrate and Epi demand to negotiate better pricing
- Innovation through design
- Reduce technology risk, encourage investments by VC firms - \$10-15 M is required to create a product as opposed to \$200 M



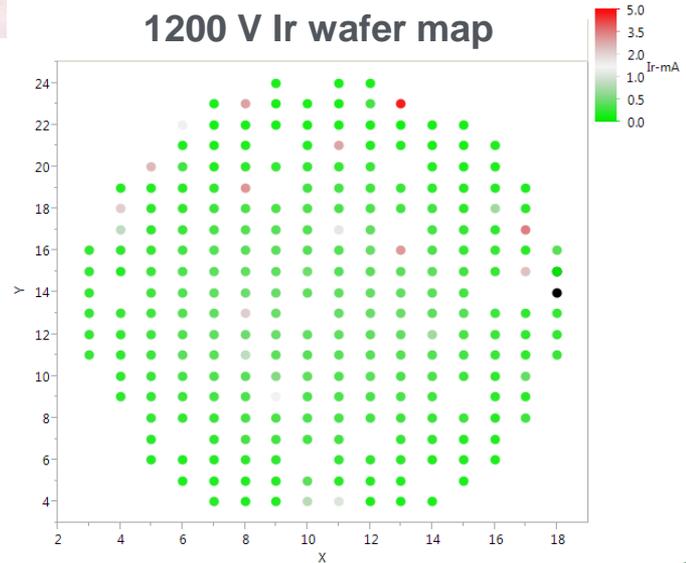
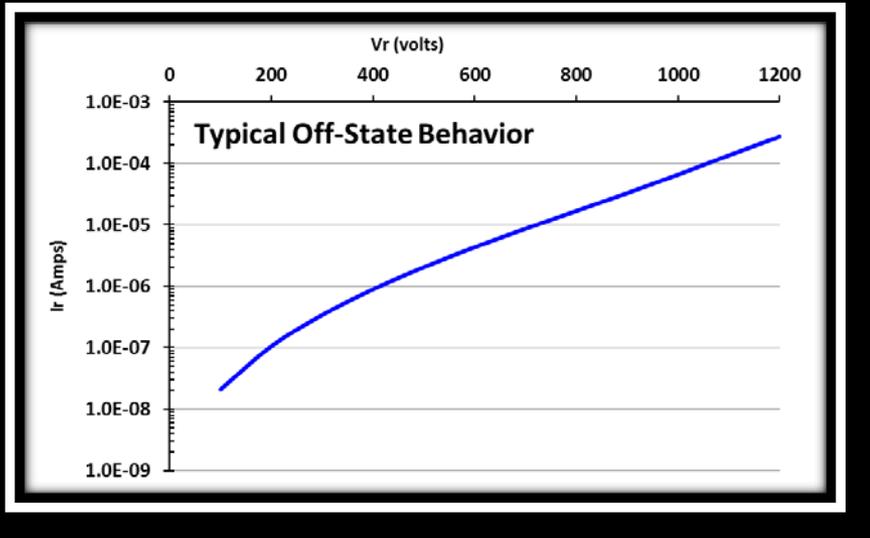
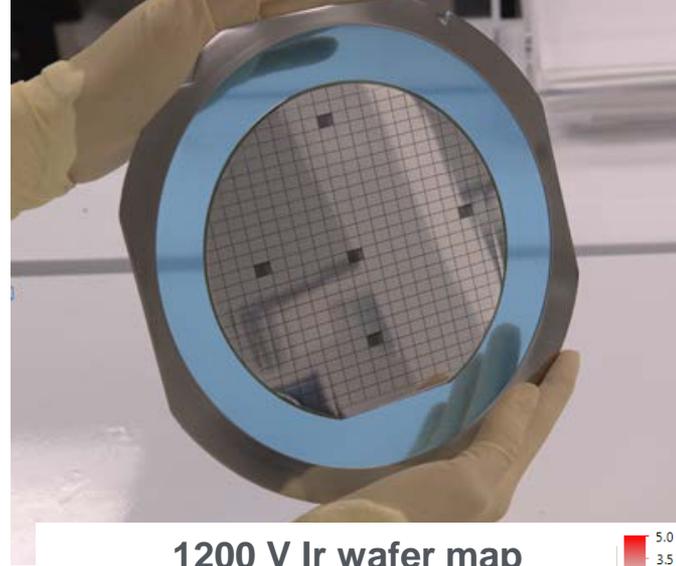
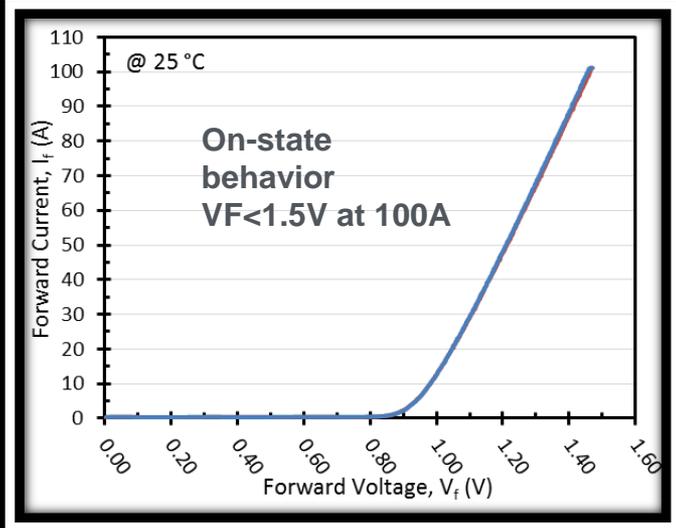
- X-FAB now **'SiC-ready'**; capable of providing complete SiC Manufacturing
- Target
  - \$850/wafer process cost in low volumes
  - \$500/wafer process cost in high volumes



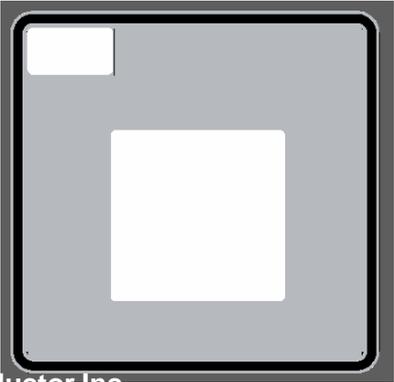
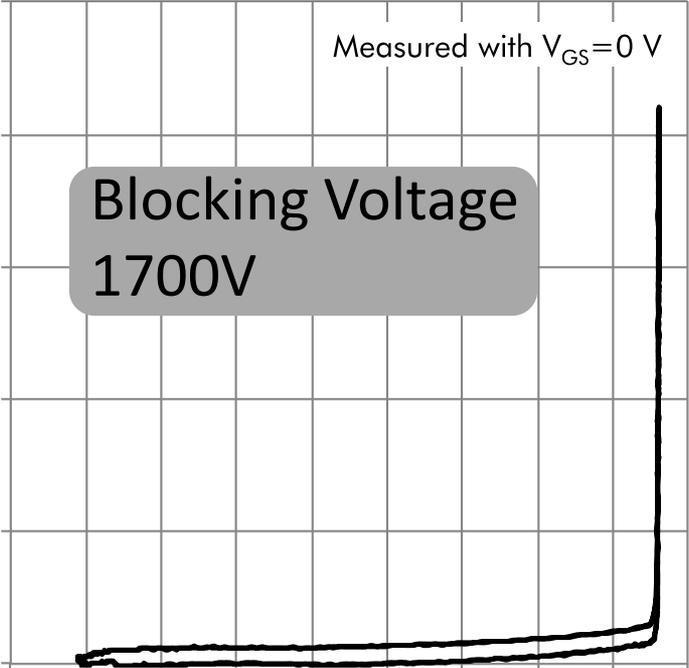
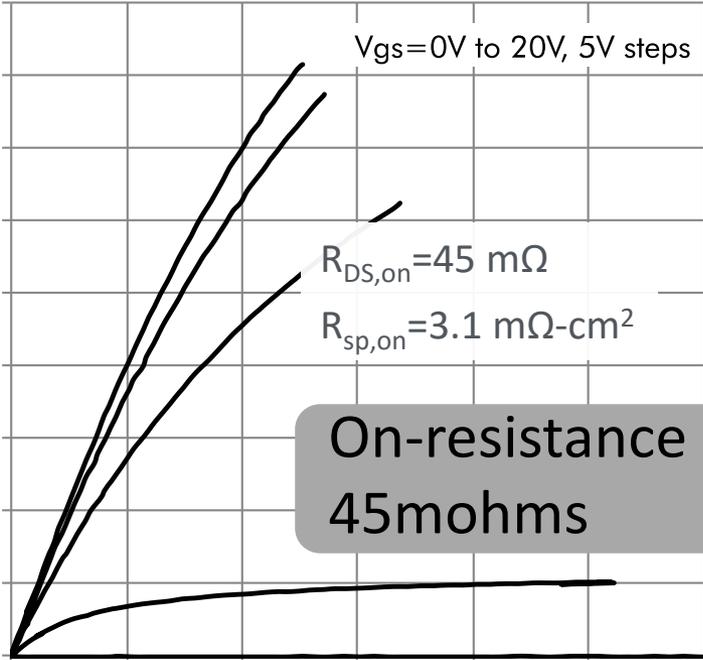
6" SiC wafer at X-FAB

# 6inch Foundry Development

## Large Area JBS Diodes 100A, 1200V



# MOSFETs fabricated in 150mm Si foundry



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# *PowerAmerica Success*

## *Stories in Power Electronics*

# SiC PV Converter



1x



Best Si commercial PV converter (~0.8 kW/kg)

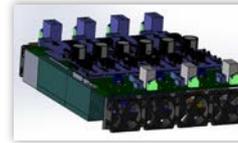


3x



FSU Gen-I SiC PV converter prototype (~2.5 kW/kg)

6x



FSU Gen-II SiC PV converter conceptual design (~5 kW/kg)

## Gen- I SiC PV converter

- ✓ 2.5 kW/kg, 22.7 W/in<sup>3</sup>
- ✓ Peak efficiency 99%
- ✓ SiC T-type module (Wolfspeed)
- ✓ Filter-less at grid side
- ✓ Low CM voltage

## Cost reduction with FSU SiC PV converter:

- Maintenance, installation, transportation and storage cost ↓ - smaller & lighter
- Filter, enclosure, heatsink cost ↓ - less metal
- Development & manufacturer cost ↓ -scalable
- Fault related energy loss ↓ - more stable

## Education/Training:

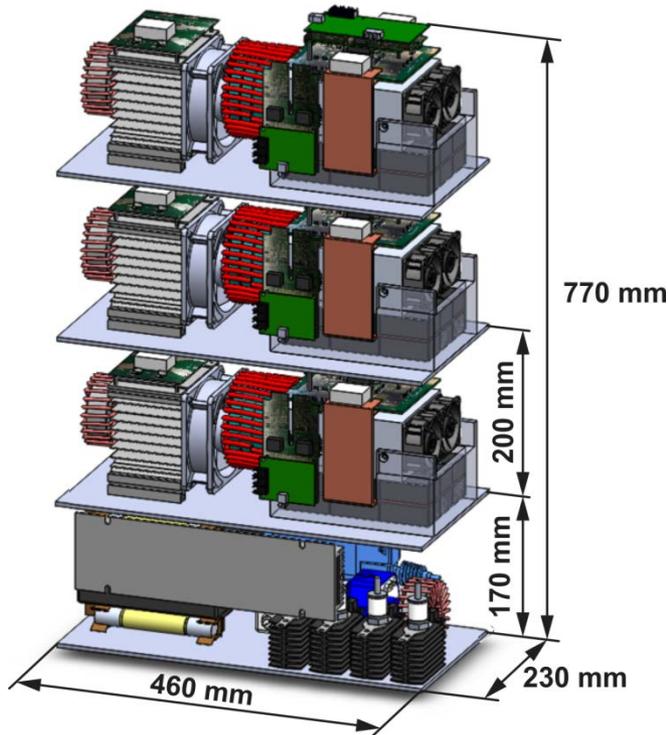
- 5 graduate students performing
  - Device characterization and protection
  - Magnetic components design
  - High sample-rate control and software design
  - Low parasitic PCB design

# Medium Voltage WBG EV Fast Charger

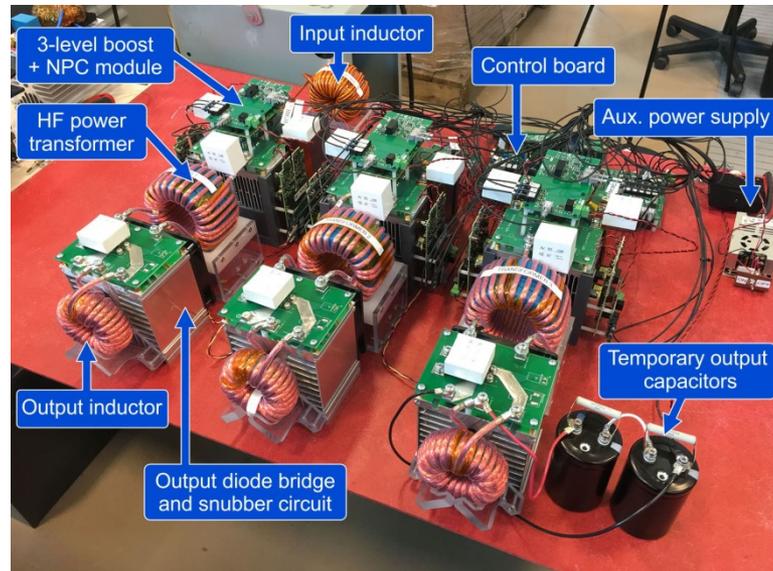
❑ **Objective:** Develop a modular medium voltage WBG EV Fast Charger using SiC semiconductor power devices to exploit the advantages of using WBG Devices

❑ MV WBG Fast charger

- 50kW; 2,400Vac to 400Vdc
- $\eta \geq 95\%$ ,  $PF \geq 0.98$ ,  $THD \leq 2\%$
- 10 x size reduction; 4x weight reduction
- Simple install w/o step-down transformer



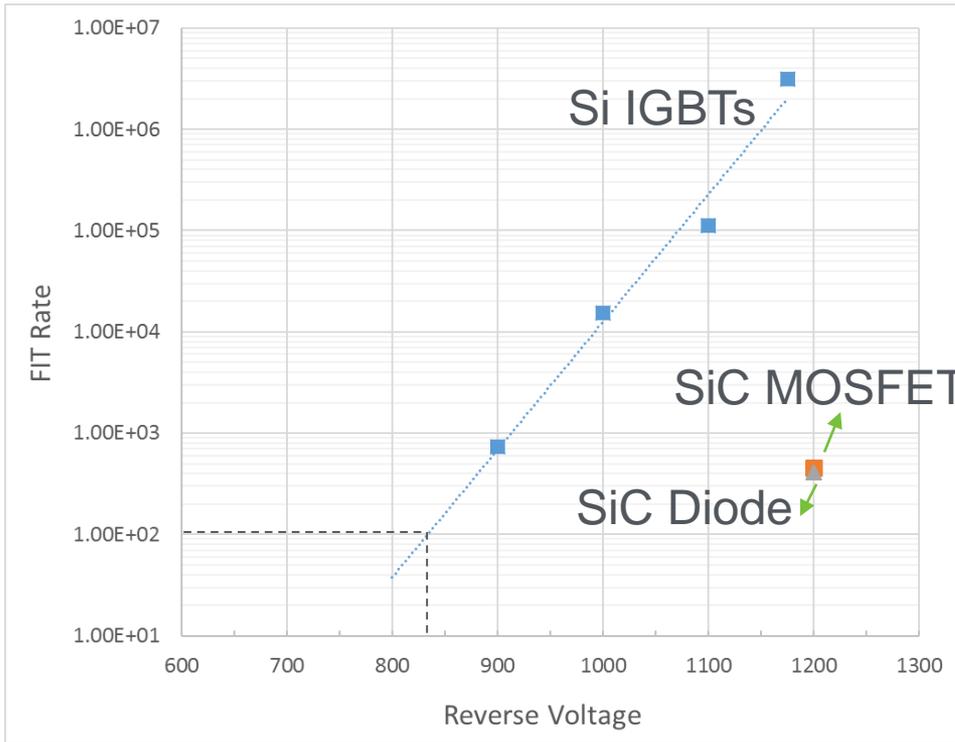
Prototype Rendering  
& Hardware Implementation



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# ***Cosmic Ray Ruggedness of WBG***

## SBIR Project



No failures were observed on SiC devices. FIT rate was calculated assuming one fail after 6 months of testing for comparison with Si IGBT failure data

- Terrestrial cosmic radiation induced failures observed on 1200V Si IGBTs at four different voltages
- To achieve a FIT rate of 100, 1200V Si IGBTs cannot be biased > 800V
- **No failures were observed on 1200V SiC MOSFETs or Diodes after testing for 6 months (over 2 million device hours) at rated voltage of 1200V!**
- Testing will continue on both 1200V SiC MOSFETs and diodes
- Future work should also focus on radiation hardness of SiC devices for space applications

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# *Traineeships*

# Wide Bandgap Traineeship--\$ 5M for 5 Yrs

- **Purpose**

- Provide hands-on training of students in WBG power electronic devices and their application.

- **Benefits**

- Ensure a pipeline of well-trained professionals entering industry and academia
- Enable a 'chain reaction' of higher education in WBG technology for decades

University of Tennessee



Virginia Polytechnic Institute



## Program Impact:

- >45 U.S. citizen M.S. and Ph.D. graduates in power engineering over 5 years
- 7 new graduate courses developed focusing on WBG
  - Converters, electrical systems packaging, WBG characterization and applications
- Students involved with National Laboratory and Industrial Internships

Goal: Train at least 100 Graduate students in 5 years

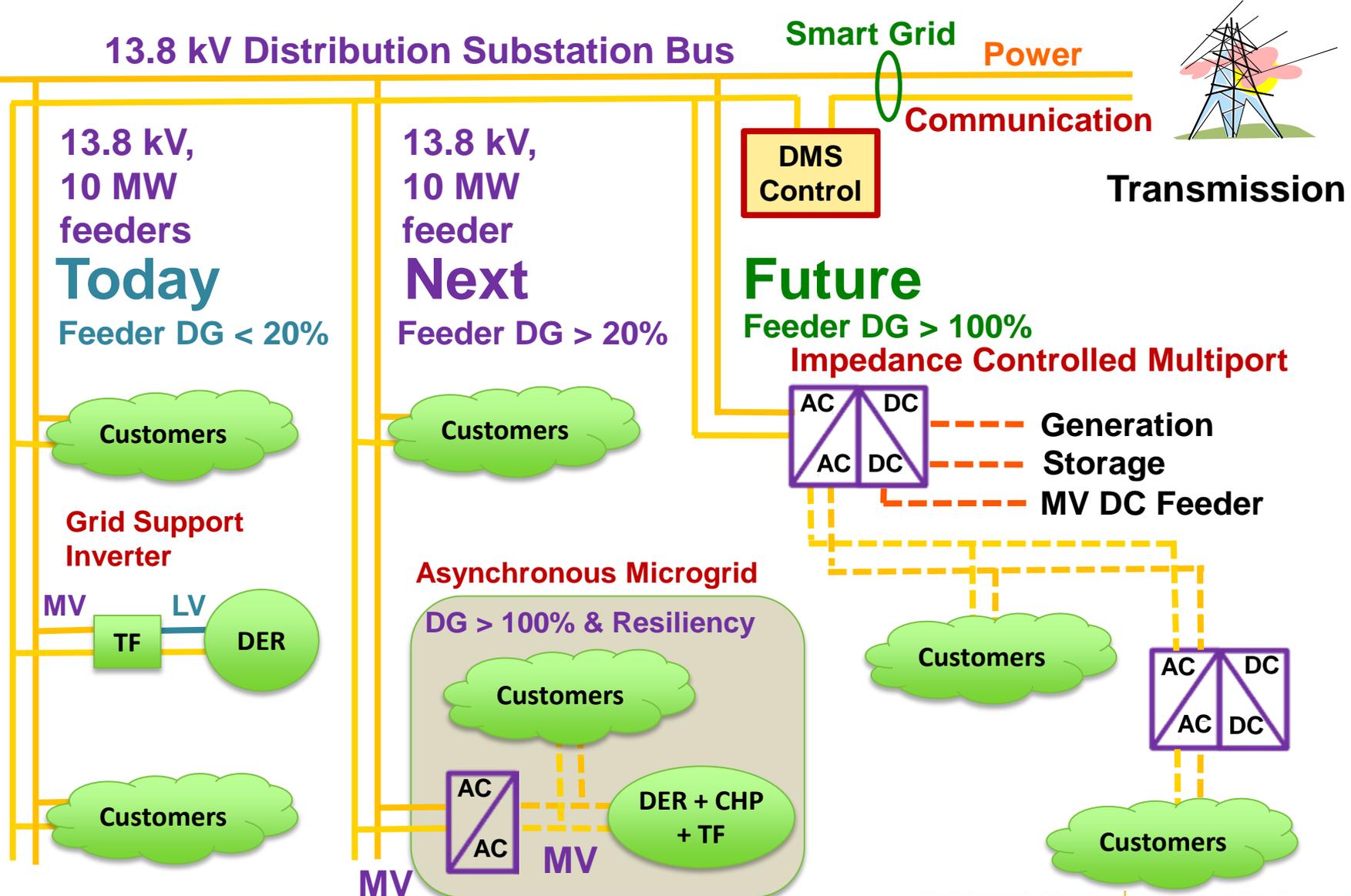
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# *Renewable Challenge And HV Devices*

# Hurricane Sandy, Oct. 2012, 285 People Dead, \$75 B loss

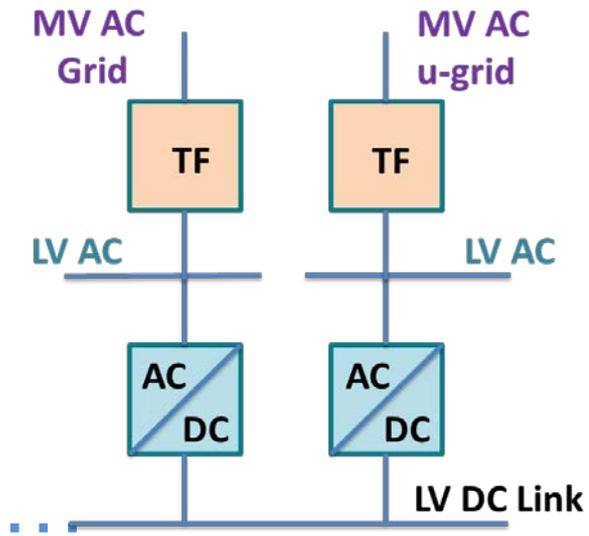


# High Penetration Distributed Generation

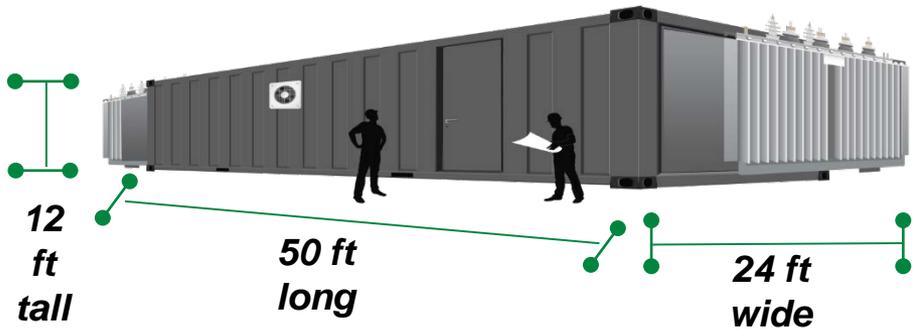


# HV SiC makes 100% Renewable Energy Affordable

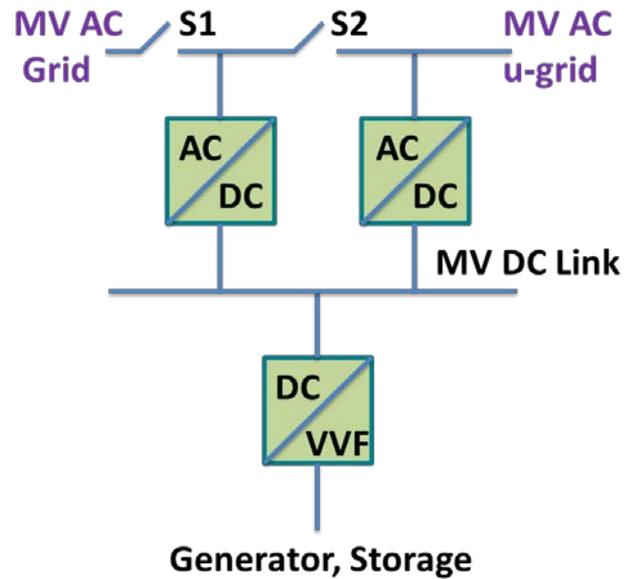
## Silicon Solution



*Example installation: 2 x 5 MVA*



## SiC Solution



### HV-HF SiC Modules enable:

- Much Smaller Size and Weight (10x)
- Lower Cost Potential
- Better Performance
  - Lower impedance
  - Higher bandwidth

# Summary

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- **Approaching a Global Energy ‘tipping’ point**
  - **Urgent need for reducing GHG**
  - **Expansion of Renewable Sources is critical**
  - **HV SiC devices necessary for realization**
- **Fabless foundry Model *WILL* reduce WBG prices and accelerate market adoption**
- **Next Big Markets: Transportation, Data Servers and Variable Speed Drives for MW Motors**
- **Educational Initiatives- essential for future workforce**